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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 10/649,046  
Filing Date: August 27, 2003  
Applicant: Berger  
Entitled: SELF-ALIGNED AND SELF-LIMITED QUANTUM DOT  
NANOSWITCHES AND METHODS FOR MAKING SAME  
Art Unit: 2811  
Examiner: Not Known  
Docket No.: OSU1159-166B

Mail Stop AMENDMENT  
Commissioner for Patents  
P.O. Box 1450  
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Trisha M. Beachy  
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Sir:

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As authorized and encouraged under 37 CFR §§ 1.97-1.98 and the provisions of MPEP §§ 609 and 707.05 (b), Applicant(s) submits herewith certain patent references, publications and/or other information which the Patent and Trademark Office may wish to consider in examining the above-identified patent application. The references and information are listed below and on attached form PTO-1449.

**U.S. PATENTS**

U.S. PATENT NUMBER	INVENTOR(S)
NONE	

**FOREIGN PATENT DOCUMENTS**

COUNTRY	PATENT NO.	INVENTOR(S)
NONE		

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A copy of each document is included for the express purpose of providing the Patent and Trademark Office with ample opportunity to evaluate the same and arrive at an independent assessment of the materiality of each, if any, to the examination of the above-identified application.

In reviewing the enclosed copies of the above documents, the Examiner is instructed to ignore any underscoring or highlighting which may have been done because

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Applicant(s) respectfully requests that the documents cited herein be made of record in the normal manner and that such documents appear on the printed patent as being considered and made of record.

Respectfully submitted,

Date: 9-20-04

By: Michael Stonebrook

Michael Stonebrook  
Registration No.: 53,851  
Standley Law Group LLP  
495 Metro Place South, Suite 210  
Dublin, Ohio 43017-5319  
Telephone: (614) 792-5555  
Facsimile: (614) 792-5536



**FORM PTO-1449 TO BE FILED WITH  
INFORMATION DISCLOSURE STATEMENT**

U.S. Department of Commerce	:	Atty. Docket No.: OSU1159-166B
Patent and Trademark Office	:	Serial No.: 10/649,046
	:	Filing Date: August 27, 2003
INFORMATION	:	Applicant: Berger
DISCLOSURE STATEMENT	:	Group Art Unit: 2811
BY APPLICANTS	:	Examiner: Not Known

**U.S. PATENT DOCUMENTS**

Examiner's Initial	Document Number	Date	Name	Class/Sub- class
	NONE			

**FOREIGN PATENT DOCUMENTS**

Examiner's Initial	Document Number	Date	Country/Name	Translation yes/no
	NONE			

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Examiner	Date Considered
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